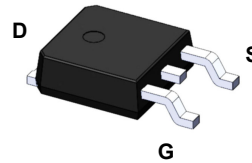
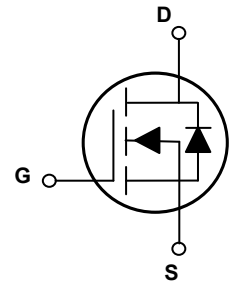


### Main Product Characteristics

$V_{(BR)DSS}$	250V
$R_{DS(ON)}$	0.62Ω (Max.)
$I_D$	6A



TO-252 (DPAK)



Schematic Diagram

### Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



### Description

The GSFD2506 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	250	V
Gate-to-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current, @ Steady-State ( $T_C=25^\circ\text{C}$ )	$I_D$	6	A
Continuous Drain Current, @ Steady-State ( $T_C=100^\circ\text{C}$ )		4.2	A
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	24	A
Power Dissipation	$P_D$	38	W
		0.31	W/°C
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	10.6	mJ
Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.29	°C/W
Operating Junction and Storage Temperature Range	$T_J/T_{STG}$	-55 to +150	°C
Lead Temperature for Soldering Purposes	$T_L$	260	°C

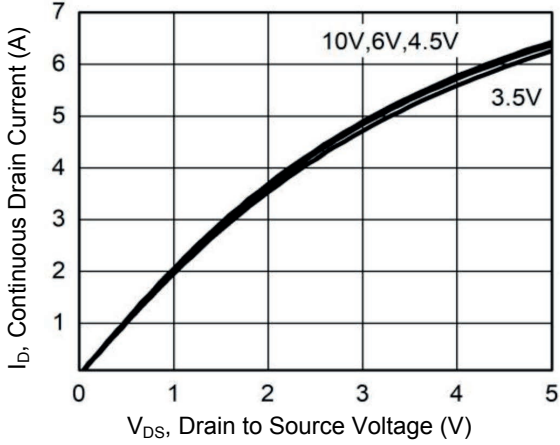
### Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>On / Off Characteristics</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	250	-	-	V
Drain-to-Source Leakage Current	$I_{DSS}$	$V_{DS}=250V, V_{GS}=0V, T_C=25^\circ\text{C}$	-	-	1.0	$\mu A$
		$V_{DS}=200V, T_C=125^\circ\text{C}$	-	-	100	$\mu A$
Gate-to-Source Forward Leakage	$I_{GSS}$	$V_{DS}=0V, V_{GS}=20V$	-	-	100	nA
		$V_{DS}=0V, V_{GS}=-20V$	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=2A$	-	0.53	0.62	$\Omega$
		$V_{GS}=4.5V, I_D=2A$	-	0.59	0.69	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	-	3.0	V
<b>Dynamic and Switching Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$	-	777	-	pF
Output Capacitance	$C_{oss}$		-	14	-	
Reverse Transfer Capacitance	$C_{rss}$		-	4.6	-	
Total Gate Charge <sup>3,4</sup>	$Q_g$	$I_D=4.0A, V_{DS}=100V, V_{GS}=10V$	-	13	-	nC
Gate-to-Source Charge <sup>3,4</sup>	$Q_{gs}$		-	2.3	-	
Gate-to-Drain ("Miller") Charge <sup>3,4</sup>	$Q_{gd}$		-	2.5	-	
Turn-On Delay Time <sup>3,4</sup>	$t_{d(on)}$	$V_{DD}=100V, V_{GS}=10V, R_G=5\Omega, I_D=5.0A$	-	14	-	nS
Rise Time <sup>3,4</sup>	$t_r$		-	11	-	
Turn-Off Delay Time <sup>3,4</sup>	$t_{d(off)}$		-	40	-	
Fall Time <sup>4,5</sup>	$t_f$		-	10	-	
Gate Resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$	-	1.6	-	$\Omega$
<b>Source-Drain Ratings and Characteristics</b>						
Continuous Source Current (Body Diode)	$I_S$	$T_C=25^\circ\text{C}$ , MOSFET symbol showing the integral reverse p-n junction diode.	-	-	6.0	A
Diode Pulse Current	$I_{SM}$		-	-	24	A
Diode Forward Voltage	$V_{SD}$	$I_S=4.0A, V_{GS}=0V$	-	-	1.3	V
Reverse Recovery Time <sup>3</sup>	$T_{rr}$	$I_S=4.0A, V_{GS}=0V, dl_F/dt=100A/\mu s$	-	86	-	nS
Reverse Recovery Charge <sup>3</sup>	$Q_{rr}$		-	0.29	-	$\mu C$

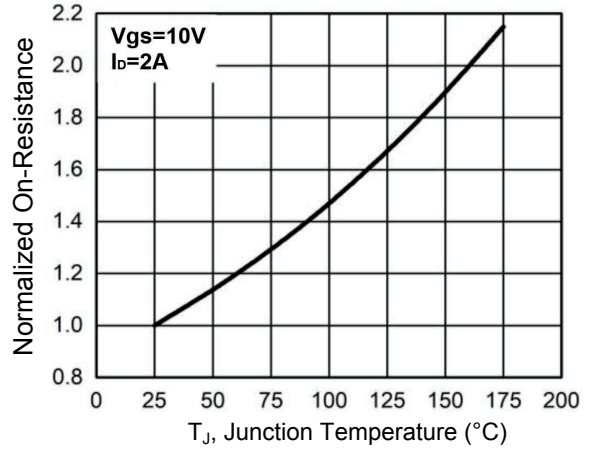
Note:

1. Pulse width limited by maximum junction temperature.
2.  $L=0.5\text{mH}$ ,  $V_{DD}=40V$ ,  $R_G=25\Omega$ , starting  $T_J=25^\circ\text{C}$ .
3. Pulse test: Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
4. Essentially independent of operating temperature.

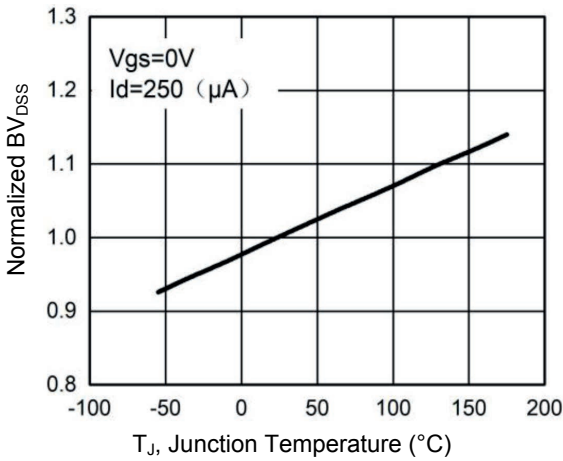
**Typical Electrical and Thermal Characteristic Curves**



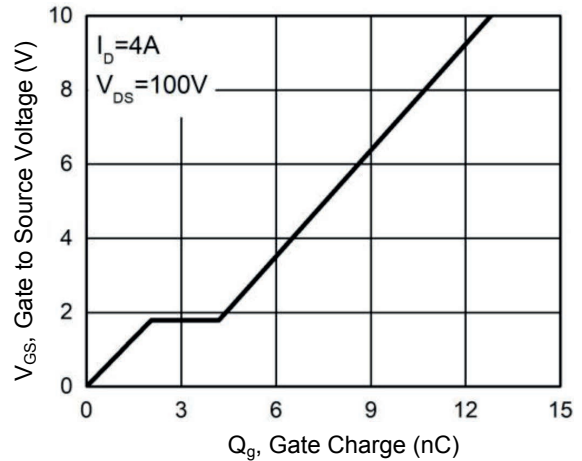
**Figure 1. Output Characteristics**



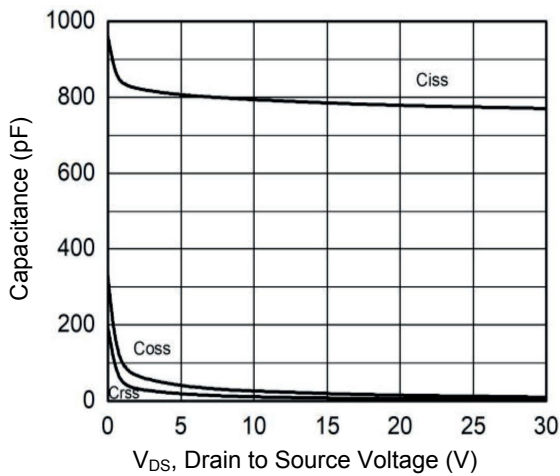
**Figure 2. Normalized  $R_{DS(ON)}$  vs.  $T_J$**



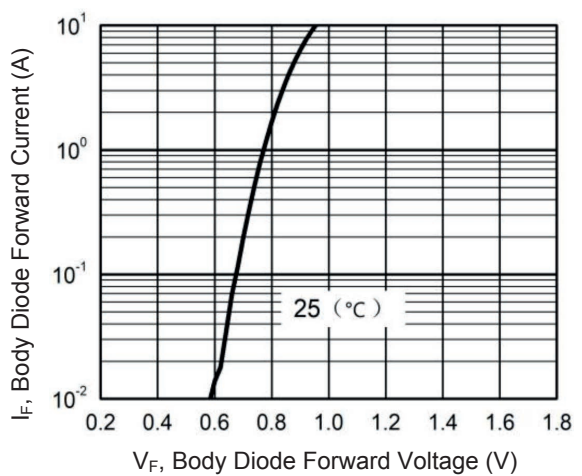
**Figure 3. Normalized  $BV_{DSS}$  vs.  $T_J$**



**Figure 4. Gate Charge Waveform**

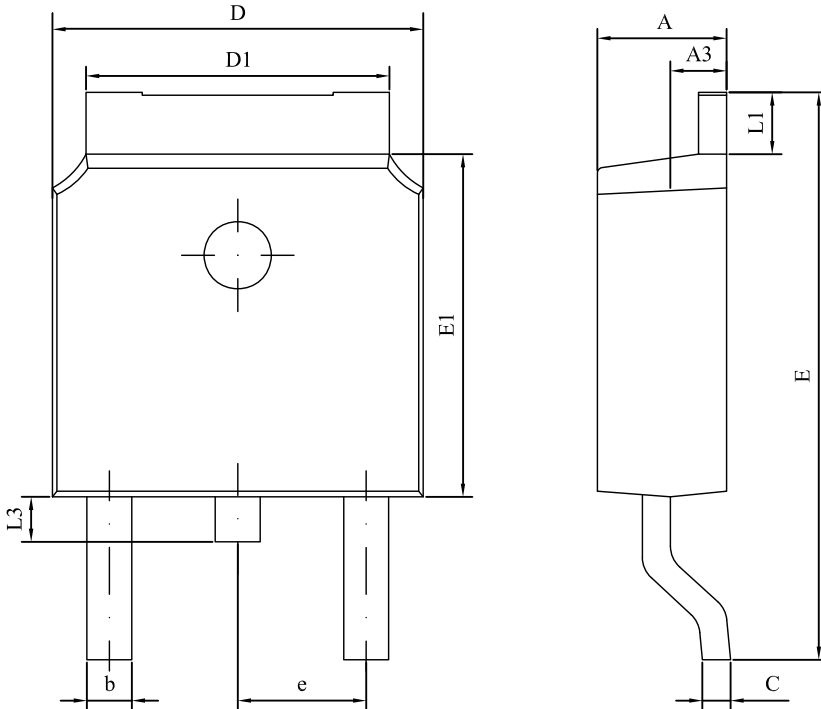


**Figure 5. Capacitance Characteristics**



**Figure 6. Body Diode Characteristics**

### Package Outline Dimensions TO-252 (DPAK)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.40	0.085	0.094
A3	0.90	1.10	0.035	0.043
b	0.50	0.90	0.020	0.035
C	0.40	0.65	0.016	0.026
D	6.30	6.90	0.248	0.272
D1	4.95	5.50	0.195	0.217
E	9.40	10.41	0.370	0.410
E1	5.90	6.30	0.232	0.248
e	2.286 BSC		0.090 BSC	
L1	0.89	1.27	0.035	0.050
L3	0.60	1.10	0.024	0.043

### Order Information

Device	Package	Marking	Packaging	SPQ
GSFD2506	TO-252 (DPAK)	D2506	Tape & Reel	2,500 Pcs / Reel

For more information, please contact us at: [inquiry@goodarksemi.com](mailto:inquiry@goodarksemi.com)